FORM HDP-1449 (Based on Form PTO-1449)

## PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Sheet 1 of 1

ATTORNEY DOCKET No.	SERIAL NO.		
9319A-001667/NP	10/579,871		
APPLICANT			
Masayasu MIYATA			
FILING DATE	GROUP		
May 18, 2006	<del>2842</del> 2895		

U.S. PATENT DOCUMENTS						
Ref. Desig.	Examiner's Initials	Document Number	Date	Name	Class/ Subclass	(If appropriate) Filing Date
1.		5,521,127	05/28/1996	Hori		
2.		6,191,463	02/20/2001	Mitani et al.		
3.		6,208,002	03/27/2001	Satake et al.		
4.		6,444,533	09/03/2002	Lyding et al.		
5.		2003/168707	09/11/2003	Sakamoto et al.		

FOREIGN PATENT DOCUMENTS							
Ref. Desig.	Examiner's Initials	Document Number	Date	Country	Class/ Subclass	Translation <sup>1</sup> Yes	* No
1.		EP 0 892 424	06/11/1998	Europe		N/A	
2.		EP 1 347 507	07/11/2002	Europe		N/A	

OTHE	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)				
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1.		"Interface-trap generation at ultrathin SiO2 interfaces during negative-bias temperature aging"; Shigeo Ogawa, Masakazu Shimaya, and Noboru Shiono; J. Appl. Phys 77 (3), 1 February 1995; 1995 American Institute of Physics, pp 1137-1148			
2.		"Improved hydrogen free chemical vapor depsoition of silicon dioxide"; Yasutaka Uchida, Kohshi Taguchi, and Masakiyo Matsumura; Journal of Non-Crystalline Solids 354 (1999) 11-16; 1999 Elsevier Science B. V.			
3.		"Effect of N2O/SiH4 ratio on the properties of low-temperature silicon oxide films from remote plasma chemical vapour deposition"; Youg-Bae Park, Jin-Kyu Kang, Shi-Woo Rhee; Thin Solid Films 280 (1996) 43-50; Elsevier Science S.A.			

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Examiner:	/Edward Wojciechowicz/	Date Considered:	08/04/2008	
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